

FFSP3065A

SiC Diode - 650V, 30A, TO-220-2

Product Overview

For complete documentation, see the data sheet.

Silicon Carbide (SiC) Schottky Diodes use a completely new technology that provides superior switching performance and higher reliability to silicon. No reverse recovery current, temperature independent switching characteristics, and excellent thermal performance sets Silicon Carbide as the next generation of power semiconductor. System benefits include highest efficiency, faster operating frequency, increased power density, reduced EMI, and reduced system size and cost.

Features

- Max Junction Temperature 175 °C
- Avalanche Rated 180 mJ
- High Surge Current Capacity
- Positive Temperature Coefficient
- No Reverse Recovery / No Forward Recovery

Applications

- PFC
- Industrial Power
- Solar
- EV Charger
- UPS

Part Electrical Specifications

Product	Pricing (\$/Unit)	Compliance	Status	Family	Configuration	V _{RRM} (V)	I _{F(ave)} (A)	V _F (Max)	I _{FSM} (A)	I _R (Max) (µA)	Package Type
FFSP3065A	6.1188		Active	D1	Single	650	30	1.75	150	200	TO-220-2